

Abstract of disclosure

Disclosure is a method for forming an alignment pattern of a semiconductor device. The method has the steps of forming a trench in each of a cell area, a peripheral circuit area, and a scribe line of a silicon substrate, depositing an oxide layer on an entire surface of the silicon substrate in such a manner that the trench formed in the cell area of the silicon substrate is filled with the oxide layer, forming a trench-type isolation layer in both cell area and peripheral circuit area of the silicon substrate by CMP the oxide layer, forming an ion implantation mask for exposing predetermined portions of the cell area, the peripheral circuit area formed on the silicon substrate and a trench portion of the scribe line filled with the oxide layer, implanting impurities into an exposed portion of the silicon substrate, which is not covered with the ion implantation mask, performing the wet dipping for an oxide layer to a resultant structure of the silicon substrate so as to recess the oxide layer filled in the trench of the scribe line, and removing the ion implantation mask.